



DMPH3010LK3

Product Summary

V(BR)DSS	R _{DS(ON)} Max	Ι _D T _C = +25°C
-30V	$7.5 m\Omega @ V_{GS} = -10V$	-50A
-30 V	$10m\Omega @ V_{GS} = -4.5V$	-45A

Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- DC-DC Converters
- Power Management Functions
- Backlighting

175°C P-CHANNEL ENHANCEMENT MODE MOSFET

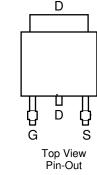
Features and Benefits

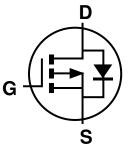
- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switch (UIS) Test in Production
- Low On-Resistance
- Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: TO252
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Finish Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (e3)
- Weight: 0.33 grams (Approximate)







Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMPH3010LK3-13	TO252	2,500/Tape & Reel

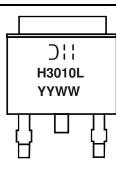
Notes: 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.

2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



>!! = Manufacturer's Marking
H3010L = Product Type Marking Code
YYWW = Date Code Marking
YY = Year (ex: 15 = 2015)
WW = Week (01 to 53)



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V _{DSS}	-30	V		
Gate-Source Voltage	V _{GSS}	±20	V		
Continuous Drain Current (Note 6), V _{GS} = -10V	Steady State	$T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$	ID	-50 -40	А
	Steady State	T _A = +25°C T _A = +100°C	ID	-16 -11	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	-100	A
Maximum Body Diode Continuous Current (Note 6)			Is	-3.5	А
Avalanche Current (Note 7), L = 0.1mH			I _{AS}	-47	A
Avalanche Energy (Note 7), L = 0.1mH			E _{AS}	113	mJ

Thermal Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)		PD	2.0	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{ heta JA}$	73	°C/W
Total Power Dissipation (Note 6)		PD	3.9	W
hermal Resistance, Junction to Ambient (Note 6) Steady State		$R_{\theta JA}$	38	°C/W
Thermal Resistance, Junction to Case		R _{0JC}	1.0	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +175	°C

Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)	•)		- 76		•		
Drain-Source Breakdown Voltage	BV _{DSS}	-30		—	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current	IDSS			-1.0	μA	$V_{DS} = -30V, V_{GS} = 0V$	
Gate-Source Leakage	IGSS	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)			•				
Gate Threshold Voltage	V _{GS(TH)}	-1.1	-1.6	-2.1	V	$V_{DS} = V_{GS}$, $I_D = -250 \mu A$	
Static Drain-Source On-Resistance		_	5.7	7.5	mΩ	$V_{GS} = -10V, I_D = -10A$	
	R _{DS(ON)}	_	7.2	10	11122	$V_{GS} = -4.5V, I_D = -10A$	
Diode Forward Voltage	V _{SD}	_	-0.65	-1.0	V	$V_{GS} = 0V, I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	Ciss		6807	—	pF		
Output Capacitance	Coss		988		pF	V _{DS} = -15V, V _{GS} = 0V, f = 1.0MHz	
Reverse Transfer Capacitance	Crss	_	647	-	pF	1 = 1.000112	
Gate Resistance	Rg	_	6.2	—	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge (V _{GS} = -4.5V)	Qg	_	66	-	nC		
Total Gate Charge (V _{GS} = -10V)	Qg	_	139	—	nC		
Gate-Source Charge	Q _{gs}	_	19.1	-	nC	$V_{DS} = -15V, I_{D} = -10A$	
Gate-Drain Charge	Q _{gd}	_	21.7	—	nC		
Turn-On Delay Time	t _{D(ON)}	_	9.0	—	ns		
Turn-On Rise Time	t _R	_	10.5	—	ns		
Turn-Off Delay Time	tD(OFF)	_	255	—	ns	$R_G = 6\Omega, I_D = -1A$	
Turn-Off Fall Time	t _F	_	95	_	ns	7	
Body Diode Reverse Recovery Time	t _{RR}		27	—	ns	I _F = -10A, di/dt = -100A/µs	
Body Diode Reverse Recovery Charge	Q _{RR}		21	_	nC	$I_F = -10A$, di/dt = -100A/µs	

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

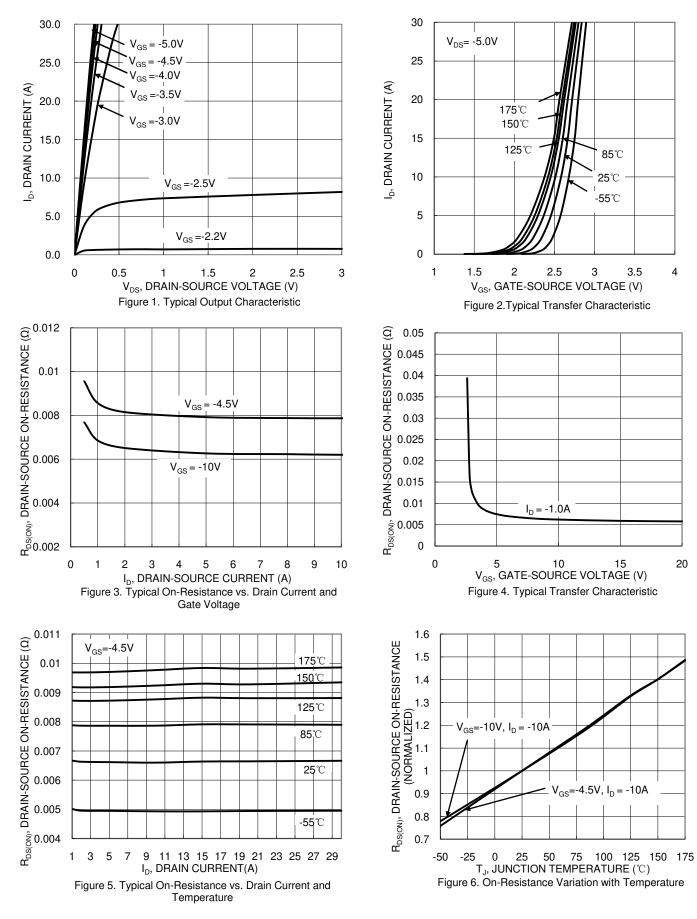
7. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep $T_J = +25^{\circ}C$.

8. Short duration pulse test used to minimize self-heating effect.

9. Guaranteed by design. Not subject to product testing.



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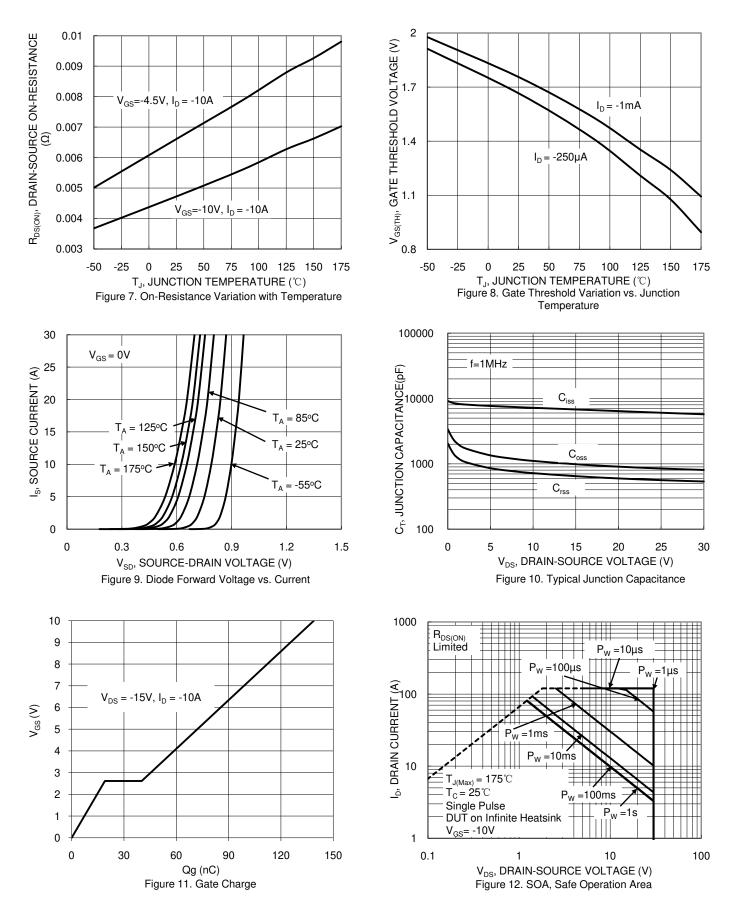
NEW PRODUCT

DMPH3010LK3 Document number: DS38123 Rev. 1 - 2

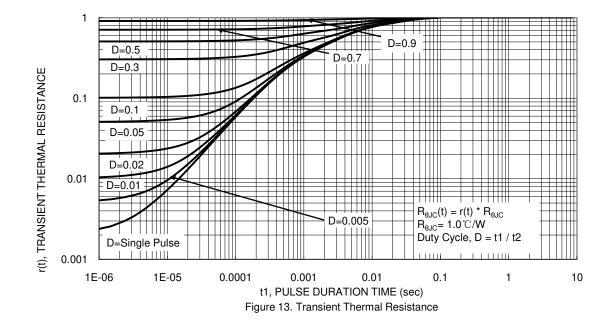


DMPH3010LK3

NEW PRODUCT



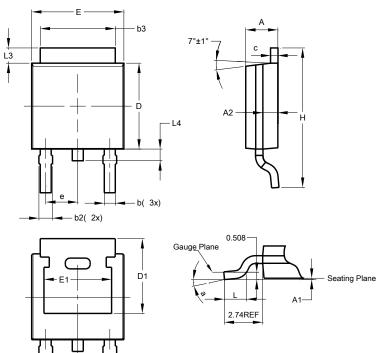






Package Outline Dimensions

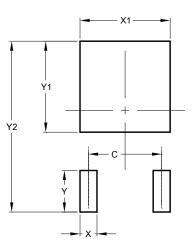
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



TO252 (DPAK)					
Dim	Min	Max	Тур		
Α	2.19	2.39	2.29		
A1	0.00	0.13	0.08		
A2	0.97	1.17	1.07		
b	0.64	0.88	0.783		
b2	0.76	1.14	0.95		
b3	5.21	5.46	5.33		
С	0.45	0.58	0.531		
D	6.00	6.20	6.10		
D1	5.21	-	-		
е	-	-	2.286		
Ε	6.45	6.70	6.58		
E1	4.32	-	-		
Н	9.40	10.41	9.91		
L	1.40	1.78	1.59		
L3	0.88	1.27	1.08		
L4	0.64	1.02	0.83		
а	0°	10°	-		
All	All Dimensions in mm				

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)				
С	4.572				
Х	1.060				
X1	5.632				
Y	2.600				
Y1	5.700				
Y2	10.700				

TO252 (DPAK)

TO252 (DPAK)



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